

XP22/XP23/XP26 Series

Nch / Pch MOSFETs

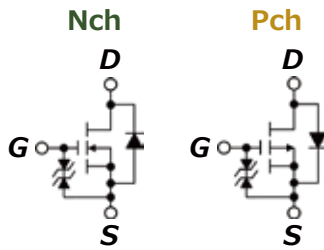
in SOT-323-3A Package



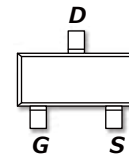
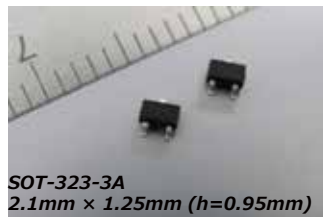
Features

- Built-in Gate Protection Diode
- Low On-State Resistance / High-Speed Switching
- Environmentally friendly :Halogen & Antimony Free / EU RoHS Compliant

Symbols



Package Information



G : Gate
S : Source
D : Drain

Applications

- General Purpose
- Switching Circuit
- Relay Circuit

N-channel MOSFETs

Ta=25°C

Status	Part	Absolute Maximum Ratings			Electrical Characteristics R _{DS(ON)} (Ω)				V _{GS(off)} (V)	
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	V _{GS} =1.5(V)	V _{GS} =2.5(V)	V _{GS} =4.5(V)	V _{GS} =10(V)	MIN.	MAX.
					TYP.	TYP.	TYP.	TYP.		
New	XP222N03013R-G	20	±8	0.3	-	1.2	0.76	-	0.4	1.3
New	XP223N10013R-G	20	±8	1	0.55	0.25	0.15	-	0.4	1.2
New	XP224N06013R-G	20	±8	0.6	-	0.38	0.25	-	0.4	1.1
New	XP231N02013R-G	30	±20	0.2	-	5.5	3	-	0.7	1.8
New	XP232N03013R-G	30	±20	0.3	-	-	1.7	1.0	0.9	2.5
New	XP233N05013R-G	30	±20	0.5	-	1.5	0.6	-	0.9	1.7
New	XP234N08013R-G	30	±20	0.8	-	-	0.3	0.2	0.9	2.6
New	XP261N70023R-G	60	±20	0.15	-	-	3.5	3.0	0.9	2.1
New	XP262N70023R-G	60	±20	0.3	-	-	1.5	1.1	1.1	2.1

P-channel MOSFETs

Ta=25°C

Status	Part	Absolute Maximum Ratings			Electrical Characteristics R _{DS(ON)} (Ω)				V _{GS(off)} (V)	
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	V _{GS} =-1.5(V)	V _{GS} =-2.5(V)	V _{GS} =-4.5(V)	V _{GS} =-10(V)	MIN.	MAX.
					TYP.	TYP.	TYP.	TYP.		
New	XP221P05013R-G	-20	±8	-0.5	-	1	0.6	-	-0.4	-1.3
New	XP222P08013R-G	-20	±8	-0.8	-	0.45	0.3	-	-0.4	-1.3
New	XP231P02013R-G	-30	±8	-0.2	-	4	3.2	-	-0.5	-1.2
New	XP232P05013R-G	-30	±8	-0.45	-	1.45	0.95	-	-0.4	-1.1

